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Coherently strained $In_{0.5}Ga_{0.5}N$ on GaN and CaO substrates are theoretically predicted to show (

structure S$\overline{3}$0: $(AC)_1/(BC)_4$ (201) SL structure.

(ii) *S*, , , *B* , : Fig. 2 shows that when one uses an end-point substrate (e.g., InGaN-on-GaN or GaAsSb-on-GaAs), provided there is coherence, the lowest energy CH habit is the ‖ one [i.e., (210)]. However, when the substrate changes to a midpoint one (as in InGaN-on-CaO or GaAsSb-on-InP), the lowest energy